

PEMH17; PUMH17

NPN/NPN resistor-equipped transistors;

R1 = 47 k Ω , R2 = 22 k Ω

Rev. 03 — 15 November 2009

Product data sheet

1. Product profile

1.1 General description

NPN/NPN Resistor-Equipped Transistors (RET).

Table 1. Product overview

Type number	Package		NPN/PNP complement	PNP/PNP complement
	NXP	JEITA		
PEMH17	SOT666	-	PEMD17	PEMB17
PUMH17	SOT363	SC-88	PUMD17	PUMB17

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

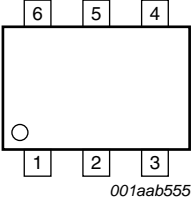
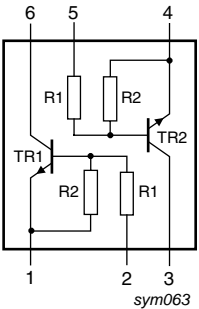
1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		33	47	61	k Ω
R2/R1	bias resistor ratio		0.37	0.47	0.57	

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1		

3. Ordering information

Table 4. Ordering information

Type number	Package		Version
	Name	Description	
PEMH17	-	plastic surface mounted package; 6 leads	SOT666
PUMH17	SC-88	plastic surface mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMH17	5T
PUMH17	H4*

- [1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
Per transistor						
V_{CBO}	collector-base voltage	open emitter	-	50	V	
V_{CEO}	collector-emitter voltage	open base	-	50	V	
V_{EBO}	emitter-base voltage	open collector	-	10	V	
V_I	input voltage					
	positive		-	+40	V	
	negative		-	-10	V	
I_O	output current (DC)		-	100	mA	
I_{CM}	peak collector current		-	100	mA	
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$				
	SOT363		[1]	-	200	mW
	SOT666		[1][2]	-	200	mW
T_{stg}	storage temperature		-65	+150	$^\circ\text{C}$	
T_j	junction temperature		-	150	$^\circ\text{C}$	
T_{amb}	ambient temperature		-65	+150	$^\circ\text{C}$	
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$				
	SOT363		[1]	-	300	mW
	SOT666		[1][2]	-	300	mW

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	625	K/W
	SOT666		[1][2]	-	625	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	416	K/W
	SOT666		[1][2]	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

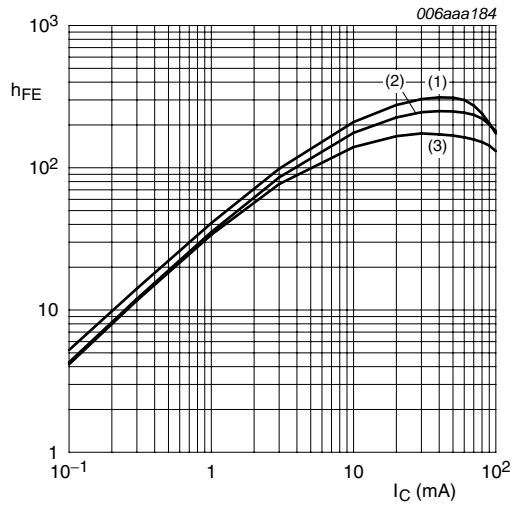
[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8. Characteristics

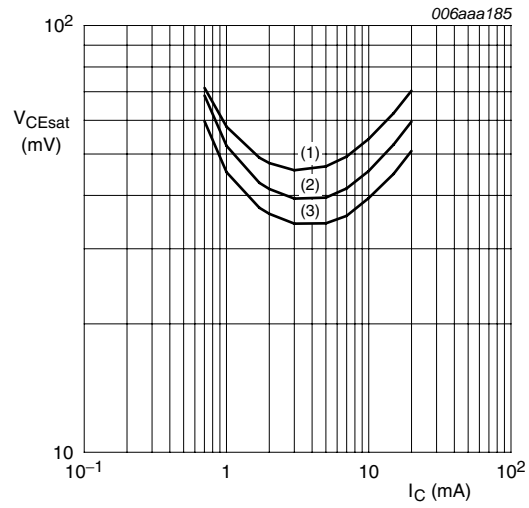
$T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
I_{CBO}	collector-base cut-off current	$V_{CB} = 50$ V; $I_E = 0$ A	-	-	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30$ V; $I_B = 0$ A	-	-	1	μ A
		$V_{CE} = 30$ V; $I_B = 0$ A; $T_j = 150$ °C	-	-	50	μ A
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5$ V; $I_C = 0$ A	-	-	110	μ A
h_{FE}	DC current gain	$V_{CE} = 5$ V; $I_C = 5$ mA	60	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10$ mA; $I_B = 0.5$ mA	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5$ V; $I_C = 100$ μ A	-	1.7	1.2	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3$ V; $I_C = 2$ mA	4	2.7	-	V
R1	bias resistor 1 (input)		33	47	61	k Ω
R2/R1	bias resistor ratio		0.37	0.47	0.57	
C_c	collector capacitance	$V_{CB} = 10$ V; $I_E = i_e = 0$ A; $f = 1$ MHz	-	-	2.5	pF



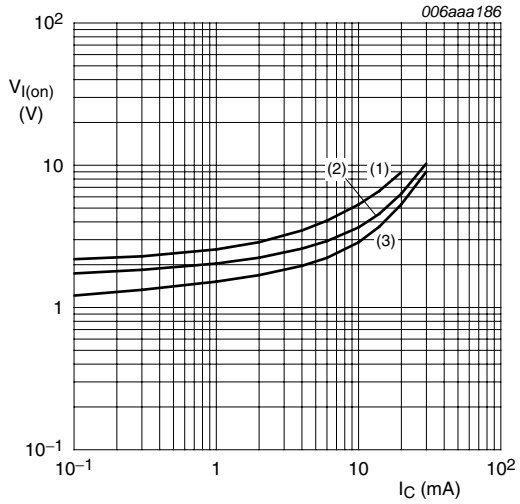
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -40\text{ °C}$

Fig. 1. DC current gain as a function of collector current; typical values



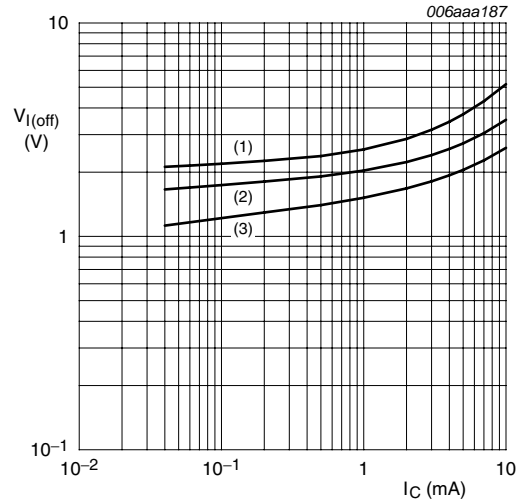
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -40\text{ °C}$

Fig. 2. Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CE} = 0.3\text{ V}$
 (1) $T_{amb} = -40\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

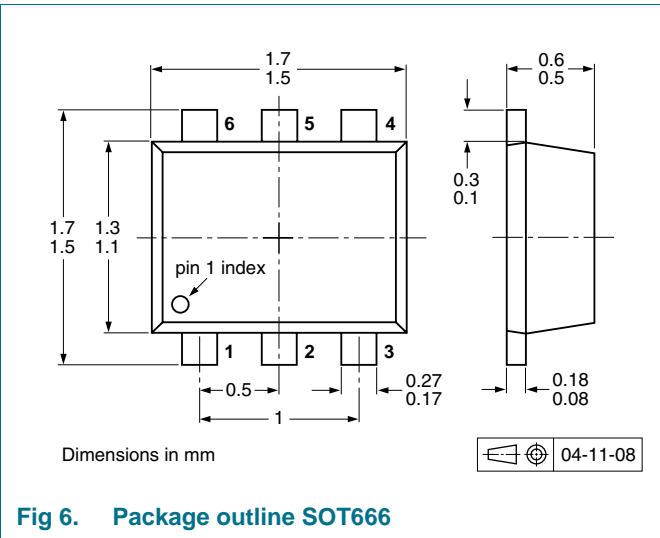
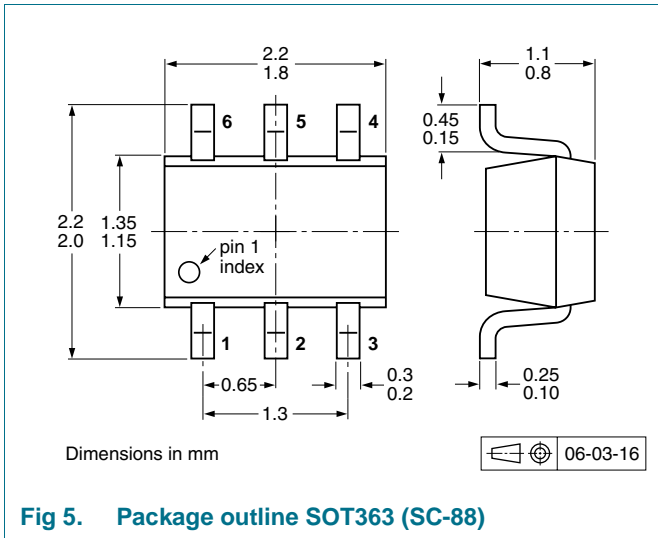
Fig. 3. On-state input voltage as a function of collector current; typical values



$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -40\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig. 4. Off-state input voltage as a function of collector current; typical values

8. Package outline



9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity			
			3000	4000	8000	10000
PEMH17	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMH17	SOT363	4 mm pitch, 8 mm tape and reel; T1 ^[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2 ^[3]	-125	-	-	-165

[1] For further information and the availability of packing methods, see [Section 12](#).

[2] T1: normal taping

[3] T2: reverse taping

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMH17_PUMH17_3	20091115	Product data sheet	-	PEMH17_PUMH17_2
Modifications:	<ul style="list-style-type: none">• This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.• Figure 5 “Package outline SOT363 (SC-88)”: updated			
PEMH17_PUMH17_2	20050503	Product data sheet	-	PUMH17_1
PUMH17_1	20031009	Product specification	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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